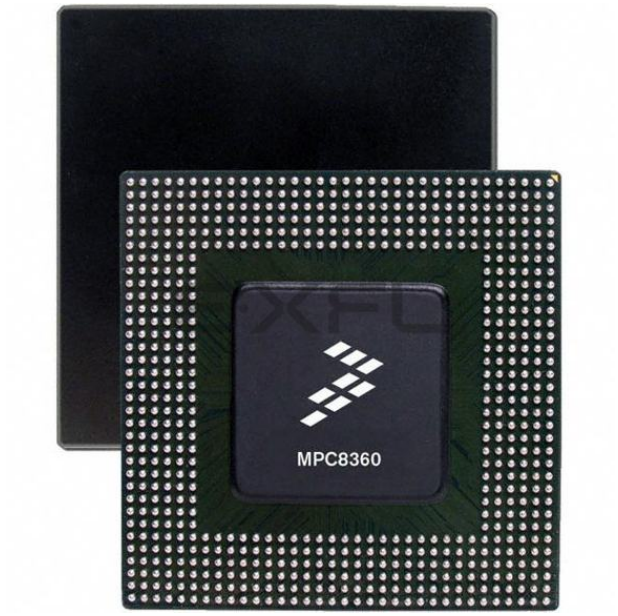

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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e300
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	533MHz
Co-Processors/DSP	Communications; QUICC Engine, Security; SEC
RAM Controllers	DDR, DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (1)
SATA	-
USB	USB 1.x (1)
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	-40°C ~ 105°C (TA)
Security Features	Cryptography, Random Number Generator
Package / Case	740-LBGA
Supplier Device Package	740-TBGA (37.5x37.5)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/kmc8360eczuajdga

- Eight TDM interfaces on the MPC8360E and four TDM interfaces on the MPC8358E with 1-bit mode for E3/T3 rates in clear channel
- Sixteen independent baud rate generators and 30 input clock pins for supplying clocks to UCC and MCC serial channels (MCC is only available on the MPC8360E)
- Four independent 16-bit timers that can be interconnected as four 32-bit timers
- Interworking functionality:
  - Layer 2 10/100-Base T Ethernet switch
  - ATM-to-ATM switching (AAL0, 2, 5)
  - Ethernet-to-ATM switching with L3/L4 support
  - PPP interworking

- Security engine is optimized to handle all the algorithms associated with IPSec, SSL/TLS, SRTP, 802.11i®, iSCSI, and IKE processing. The security engine contains four crypto-channels, a controller, and a set of crypto execution units (EUs).
  - Public key execution unit (PKEU) supporting the following:
    - RSA and Diffie-Hellman
    - Programmable field size up to 2048 bits
    - Elliptic curve cryptography
    - F2m and F(p) modes
    - Programmable field size up to 511 bits
  - Data encryption standard execution unit (DEU)
    - DES, 3DES
    - Two key (K1, K2) or three key (K1, K2, K3)
    - ECB and CBC modes for both DES and 3DES
  - Advanced encryption standard unit (AESU)
  - Implements the Rinjdael symmetric key cipher
  - Key lengths of 128, 192, and 256 bits, two key
    - ECB, CBC, CCM, and counter modes
  - ARC four execution unit (AFEU)
    - Implements a stream cipher compatible with the RC4 algorithm
    - 40- to 128-bit programmable key
  - Message digest execution unit (MDEU)
    - SHA with 160-, 224-, or 256-bit message digest
    - MD5 with 128-bit message digest
    - HMAC with either SHA or MD5 algorithm
  - Random number generator (RNG)
  - Four crypto-channels, each supporting multi-command descriptor chains
    - Static and/or dynamic assignment of crypto-execution units via an integrated controller
    - Buffer size of 256 bytes for each execution unit, with flow control for large data sizes
  - Storage/NAS XOR parity generation accelerator for RAID applications
- Dual DDR SDRAM memory controllers on the MPC8360E and a single DDR SDRAM memory controller on the MPC8358E
  - Programmable timing supporting both DDR1 and DDR2 SDRAM
  - On the MPC8360E, the DDR buses can be configured as two 32-bit buses or one 64-bit bus; on the MPC8358E, the DDR bus can be configured as a 32- or 64-bit bus
  - 32- or 64-bit data interface, up to 333 MHz (for the MPC8360E) and 266 MHz (for the MPC8358E) data rate
  - Four banks of memory, each up to 1 Gbyte

- DRAM chip configurations from 64 Mbits to 1 Gigabit with ×8/×16 data ports
- Full ECC support (when the MPC8360E is configured as 2×32-bit DDR memory controllers, both support ECC)
- Page mode support (up to 16 simultaneous open pages for DDR1, up to 32 simultaneous open pages for DDR2)
- Contiguous or discontiguous memory mapping
- Read-modify-write support
- Sleep mode support for self refresh SDRAM
- Supports auto refreshing
- Supports source clock mode
- On-the-fly power management using CKE
- Registered DIMM support
- 2.5-V SSTL2 compatible I/O for DDR1, 1.8-V SSTL2 compatible I/O for DDR2
- External driver impedance calibration
- On-die termination (ODT)

- PCI interface
  - PCI Specification Revision 2.3 compatible
  - Data bus widths:
    - Single 32-bit data PCI interface that operates at up to 66 MHz
  - PCI 3.3-V compatible (not 5-V compatible)
  - PCI host bridge capabilities on both interfaces
  - PCI agent mode supported on PCI interface
  - Support for PCI-to-memory and memory-to-PCI streaming
  - Memory prefetching of PCI read accesses and support for delayed read transactions
  - Support for posting of processor-to-PCI and PCI-to-memory writes
  - On-chip arbitration, supporting five masters on PCI
  - Support for accesses to all PCI address spaces
  - Parity support
  - Selectable hardware-enforced coherency
  - Address translation units for address mapping between host and peripheral
  - Dual address cycle supported when the device is the target
  - Internal configuration registers accessible from PCI
- Local bus controller (LBC)
  - Multiplexed 32-bit address and data operating at up to 133 MHz
  - Eight chip selects support eight external slaves
  - Up to eight-beat burst transfers
  - 32-, 16-, and 8-bit port sizes are controlled by an on-chip memory controller
  - Three protocol engines available on a per chip select basis:
    - General-purpose chip select machine (GPCM)
    - Three user programmable machines (UPMs)
    - Dedicated single data rate SDRAM controller
  - Parity support
  - Default boot ROM chip select with configurable bus width (8-, 16-, or 32-bit)
- Programmable interrupt controller (PIC)
  - Functional and programming compatibility with the MPC8260 interrupt controller
  - Support for 8 external and 35 internal discrete interrupt sources
  - Support for one external (optional) and seven internal machine checkstop interrupt sources

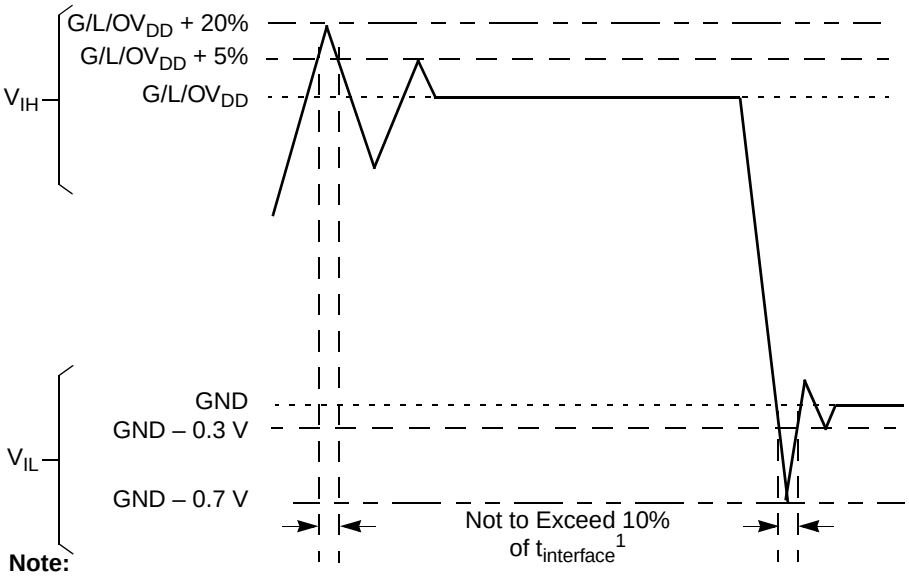
Table 2. Recommended Operating Conditions (continued)

Characteristic	Symbol	Recommended Value	Unit	Notes
PCI, local bus, DUART, system control and power management, I^2C, SPI, and JTAG I/O voltage	OV_{DD}	3.3 V ± 330 mV	V	—
Junction temperature	T_J	0 to 105 –40 to 105	°C	2

Notes:

1. GV_{DD}, LV_{DD}, OV_{DD}, AV_{DD}, and V_{DD} must track each other and must vary in the same direction—either in the positive or negative direction.
2. The operating conditions for junction temperature, T_J, on the 600/333/400 MHz and 500/333/500 MHz on rev. 2.0 silicon is 0° to 70 °C. Refer to Errata General9 in *Chip Errata for the MPC8360E, Rev. 1*.
3. For more information on Part Numbering, refer to Table 80.

This figure shows the undershoot and overshoot voltages at the interfaces of the device.



Note:
1. Note that $t_{interface}$ refers to the clock period associated with the bus clock interface.

Figure 3. Overshoot/Undershoot Voltage for $GV_{DD}/OV_{DD}/LV_{DD}$

Table 4. MPC8360E TBGA Core Power Dissipation[1] (continued)

Core Frequency (MHz)	CSB Frequency (MHz)	QUICC Engine Frequency (MHz)	Typical	Maximum	Unit	Notes
667	333	500	6.1	6.8	W	2, 3, 5, 9

Notes:
1. The values do not include I/O supply power (OV_{DD}, LV_{DD}, GV_{DD}) or AV_{DD}. For I/O power values, see Table 6.
2. Typical power is based on a voltage of V_{DD} = 1.2 V or 1.3 V, a junction temperature of T_J = 105° C, and a Dhrystone benchmark application.
3. Thermal solutions need to design to a value higher than typical power on the end application, T_A target, and I/O power.
4. Maximum power is based on a voltage of V_{DD} = 1.2 V, WC process, a junction T_J = 105° C, and an artificial smoke test.
5. Maximum power is based on a voltage of V_{DD} = 1.3 V for applications that use 667 MHz (CPU)/500 (QE) with WC process, a junction T_J = 105° C, and an artificial smoke test.
6. Typical power is based on a voltage of V_{DD} = 1.3 V, a junction temperature of T_J = 70° C, and a Dhrystone benchmark application.
7. Maximum power is based on a voltage of V_{DD} = 1.3 V for applications that use 667 MHz (CPU) or 500 (QE) with WC process, a junction T_J = 70° C, and an artificial smoke test.
8. This frequency combination is only available for rev. 2.0 silicon.
9. This frequency combination is not available for rev. 2.0 silicon.

Table 5. MPC8358E TBGA Core Power Dissipation[1]

Core Frequency (MHz)	CSB Frequency (MHz)	QUICC Engine Frequency (MHz)	Typical	Maximum	Unit	Notes
266	266	300	4.1	4.5	W	2, 3, 4
400	266	400	4.5	5.0	W	2, 3, 4

Notes:
1. The values do not include I/O supply power (OV_{DD}, LV_{DD}, GV_{DD}) or AV_{DD}. For I/O power values, see Table 6.
2. Typical power is based on a voltage of V_{DD} = 1.2 V, a junction temperature of T_J = 105° C, and a Dhrystone benchmark application.
3. Thermal solutions need to design to a value higher than typical power on the end application, T_A target, and I/O power.
4. Maximum power is based on a voltage of V_{DD} = 1.2 V, WC process, a junction T_J = 105° C, and an artificial smoke test.

Table 9. GTX_CLK125 AC Timing Specifications

At recommended operating conditions with LV_{DD} = 2.5 ± 0.125 mV/ 3.3 V ± 165 mV (continued)

Parameter/Condition	Symbol	Min	Typical	Max	Unit	Notes
GTX_CLK rise and fall time LV_{DD} = 2.5 V LV_{DD} = 3.3 V	t_{G125R}/t_{G125F}	—	—	 0.75 1.0	ns	1
GTX_CLK125 duty cycle GMII & TBI 1000Base-T for RGMII & RTBI	t_{G125H}/t_{G125}	 45 47	—	 55 53	%	2
GTX_CLK125 jitter	—	—	—	±150	ps	2

Notes:

1. Rise and fall times for GTX_CLK125 are measured from 0.5 and 2.0 V for LV_{DD} = 2.5 V and from 0.6 and 2.7 V for LV_{DD} = 3.3 V.
2. GTX_CLK125 is used to generate the GTX clock for the UCC Ethernet transmitter with 2% degradation. The GTX_CLK125 duty cycle can be loosened from 47%/53% as long as the PHY device can tolerate the duty cycle generated by GTX_CLK. See Section 8.2.2, “MII AC Timing Specifications,” Section 8.2.3, “RMII AC Timing Specifications,” and Section 8.2.5, “RGMII and RTBI AC Timing Specifications” for the duty cycle for 10Base-T and 100Base-T reference clock.

5 RESET Initialization

This section describes the DC and AC electrical specifications for the reset initialization timing and electrical requirements of the MPC8360E/58E.

5.1 RESET DC Electrical Characteristics

This table provides the DC electrical characteristics for the RESET pins of the device.

Table 10. RESET Pins DC Electrical Characteristics [1]

Characteristic	Symbol	Condition	Min	Max	Unit
Input high voltage	V_{IH}	—	2.0	OV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	–0.3	0.8	V
Input current	I_{IN}	—	—	±10	μA
Output high voltage	V_{OH}[2]	I_{OH} = –8.0 mA	2.4	—	V
Output low voltage	V_{OL}	I_{OL} = 8.0 mA	—	0.5	V
Output low voltage	V_{OL}	I_{OL} = 3.2 mA	—	0.4	V

Notes:

1. This table applies for pins $\overline{\text{PORESET}}$, $\overline{\text{HRESET}}$, $\overline{\text{SRESET}}$, and $\overline{\text{QUIESCE}}$.
2. $\overline{\text{HRESET}}$ and $\overline{\text{SRESET}}$ are open drain pins, thus V_{OH} is not relevant for those pins.

6.1 DDR and DDR2 SDRAM DC Electrical Characteristics

This table provides the recommended operating conditions for the DDR2 SDRAM component(s) of the device when GV_{DD}(typ) = 1.8 V.

Table 14. DDR2 SDRAM DC Electrical Characteristics for GV_{DD}(typ) = 1.8 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	GV_{DD}	1.71	1.89	V	1
I/O reference voltage	MV_{REF}	0.49 × GV_{DD}	0.51 × GV_{DD}	V	2
I/O termination voltage	V_{TT}	MV_{REF} – 0.04	MV_{REF} + 0.04	V	3
Input high voltage	V_{IH}	MV_{REF} + 0.125	GV_{DD} + 0.3	V	—
Input low voltage	V_{IL}	–0.3	MV_{REF} – 0.125	V	—
Output leakage current	I_{OZ}	—	±10	µA	4
Output high current (V_{OUT} = 1.420 V)	I_{OH}	–13.4	—	mA	—
Output low current (V_{OUT} = 0.280 V)	I_{OL}	13.4	—	mA	—
MV_{REF} input leakage current	I_{VREF}	—	±10	µA	—
Input current (0 V ≤ V_{IN} ≤ GV_{DD})	I_{IN}	—	±10	µA	—

Notes:

1. GV_{DD} is expected to be within 50 mV of the DRAM GV_{DD} at all times.
2. MV_{REF} is expected to equal 0.5 × GV_{DD}, and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on MV_{REF} cannot exceed ±2% of the DC value.
3. V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to equal MV_{REF}. This rail should track variations in the DC level of MV_{REF}.
4. Output leakage is measured with all outputs disabled, 0 V ≤ V_{OUT} ≤ GV_{DD}.

This table provides the DDR2 capacitance when GV_{DD}(typ) = 1.8 V.

Table 15. DDR2 SDRAM Capacitance for GV_{DD}(typ)=1.8 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input/output capacitance: DQ, DQS, $\overline{DQS}$	C_{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS, $\overline{DQS}$	C_{DIO}	—	0.5	pF	1

Note:

1. This parameter is sampled. GV_{DD} = 1.8 V ± 0.090 V, f = 1 MHz, T_A = 25°C, V_{OUT} = GV_{DD}/2, V_{OUT} (peak-to-peak) = 0.2 V.

This table provides the recommended operating conditions for the DDR SDRAM component(s) of the device when GV_{DD}(typ) = 2.5 V.

Table 16. DDR SDRAM DC Electrical Characteristics for GV_{DD}(typ) = 2.5 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	GV_{DD}	2.375	2.625	V	1
I/O reference voltage	MV_{REF}	0.49 × GV_{DD}	0.51 × GV_{DD}	V	2
I/O termination voltage	V_{TT}	MV_{REF} – 0.04	MV_{REF} + 0.04	V	3

8.2.4.1 TBI Transmit AC Timing Specifications

This table provides the TBI transmit AC timing specifications.

Table 33. TBI Transmit AC Timing Specifications

At recommended operating conditions with LV_{DD}/OV_{DD} of 3.3 V ± 10%.

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit	Notes
GTX_CLK clock period	t_{TTX}	—	8.0	—	ns	—
GTX_CLK duty cycle	t_{TTXH}/t_{TTX}	40	—	60	%	—
GTX_CLK to TBI data TCG[9:0] delay	t_{TTKHDX} t_{TTKHDV}	1.0 —	—	— 5.0	ns	3
GTX_CLK clock rise time, (20% to 80%)	t_{TTXR}	—	—	1.0	ns	—
GTX_CLK clock fall time, (80% to 20%)	t_{TTXF}	—	—	1.0	ns	—
GTX_CLK125 reference clock period	t_{G125}	—	8.0	—	ns	2
GTX_CLK125 reference clock duty cycle	t_{G125H}/t_{G125}	45	—	55	ns	—

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{TTKHDV} symbolizes the TBI transmit timing (TT) with respect to the time from t_{TTX} (K) going high (H) until the referenced data signals (D) reach the valid state (V) or setup time. Also, t_{TTKHDX} symbolizes the TBI transmit timing (TT) with respect to the time from t_{TTX} (K) going high (H) until the referenced data signals (D) reach the invalid state (X) or hold time. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{TTX} represents the TBI (T) transmit (TX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. This symbol is used to represent the external GTX_CLK125 and does not follow the original symbol naming convention.
3. In rev. 2.0 silicon, due to errata, t_{TTKHDX} minimum is 0.7 ns for UCC1. Refer to Errata *QE_ENET19* in *Chip Errata for the MPC8360E, Rev. 1*.

This figure shows the TBI transmit AC timing diagram.

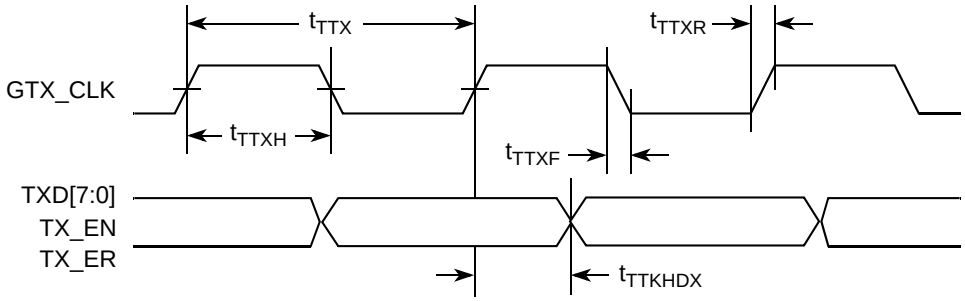


Figure 18. TBI Transmit AC Timing Diagram

This figure shows the RGMII and RTBI AC timing and multiplexing diagrams.

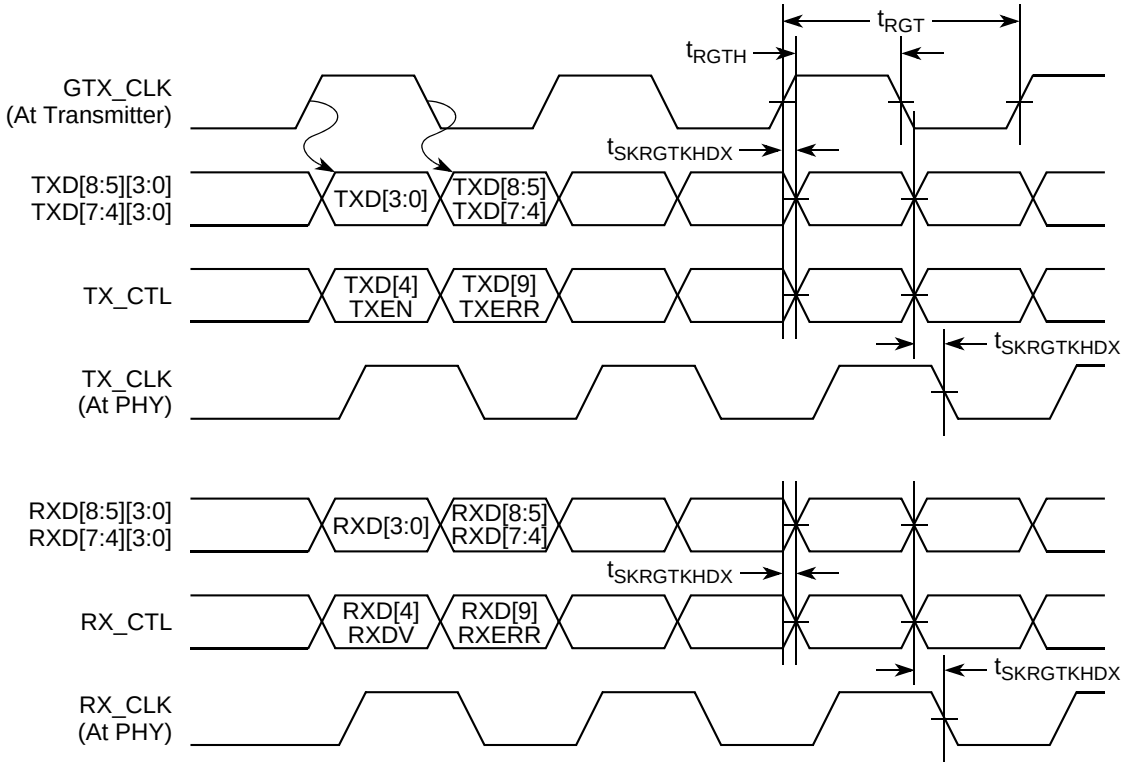


Figure 20. RGMII and RTBI AC Timing and Multiplexing Diagrams

8.3 Ethernet Management Interface Electrical Characteristics

The electrical characteristics specified here apply to MII management interface signals MDIO (management data input/output) and MDC (management data clock). The electrical characteristics for GMII, RGMII, TBI, and RTBI are specified in Section 8.1, "Three-Speed Ethernet Controller (10/100/1000 Mbps)— GMII/MII/RMII/TBI/RGMII/RTBI Electrical Characteristics."

8.3.1 MII Management DC Electrical Characteristics

The MDC and MDIO are defined to operate at a supply voltage of 3.3 V. The DC electrical characteristics for MDIO and MDC are provided in this table.

Table 36. MII Management DC Electrical Characteristics When Powered at 3.3 V

Parameter	Symbol	Conditions		Min	Max	Unit
Supply voltage (3.3 V)	OV_{DD}	—		2.97	3.63	V
Output high voltage	V_{OH}	I_{OH} = –1.0 mA	OV_{DD} = Min	2.10	OV_{DD} + 0.3	V
Output low voltage	V_{OL}	I_{OL} = 1.0 mA	OV_{DD} = Min	GND	0.50	V
Input high voltage	V_{IH}	—		2.00	—	V
Input low voltage	V_{IL}	—		—	0.80	V
Input current	I_{IN}	$0 V \le V_{IN} \le OV_{DD}$		—	±10	μA

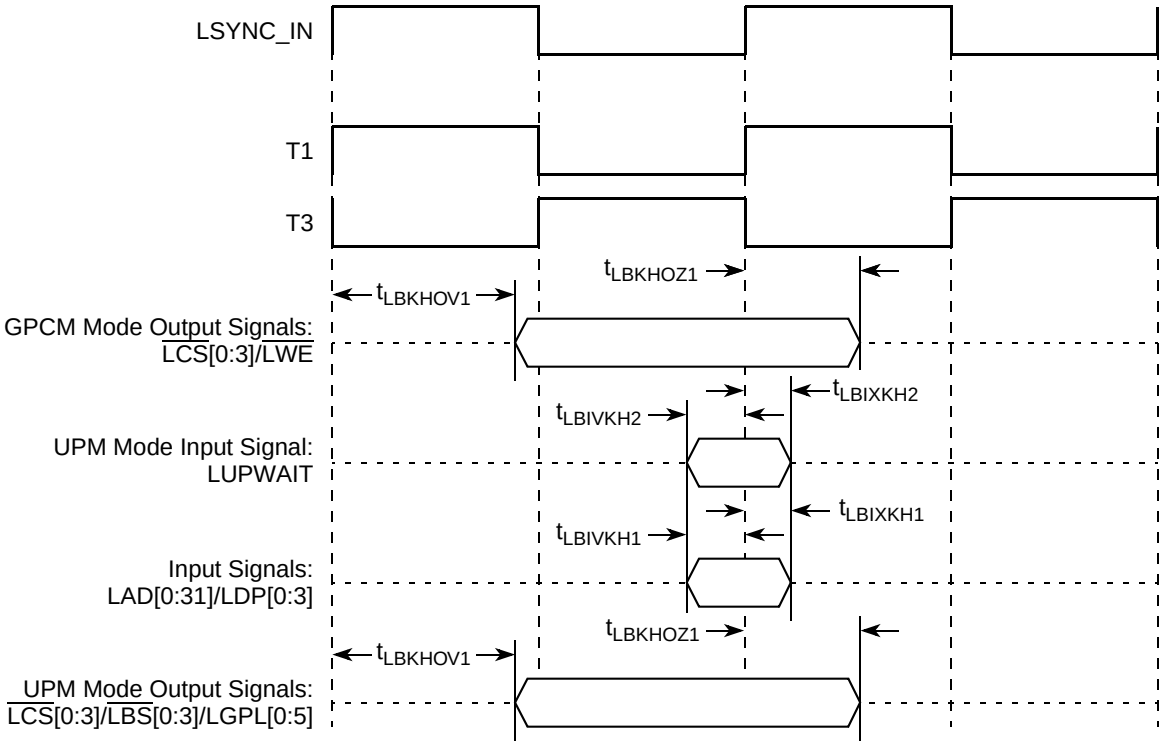


Figure 25. Local Bus Signals, GPCM/UPM Signals for LCRR[CLKDIV] = 2 (DLL Enabled)

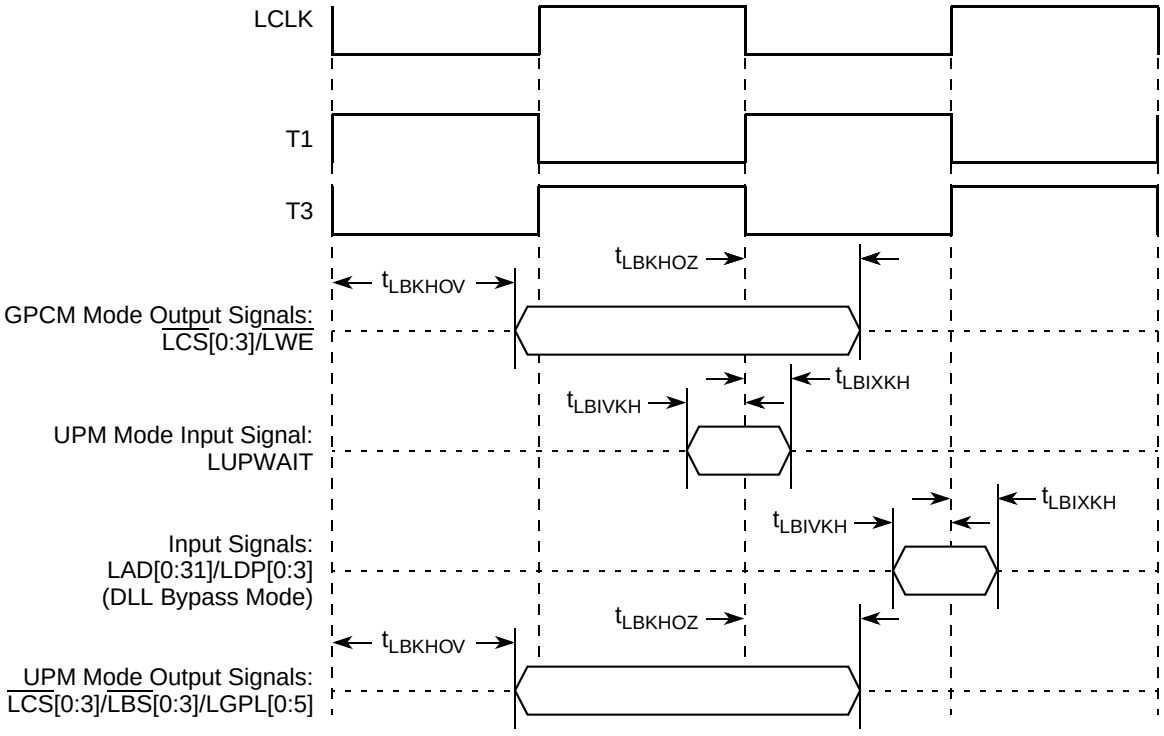


Figure 26. Local Bus Signals, GPCM/UPM Signals for LCRR[CLKDIV] = 2 (DLL Bypass Mode)

10.2 JTAG AC Electrical Characteristics

This section describes the AC electrical specifications for the IEEE 1149.1 (JTAG) interface of the device.

This table provides the JTAG AC timing specifications as defined in Figure 30 through Figure 33.

Table 43. JTAG AC Timing Specifications (Independent of CLKIN)[1]

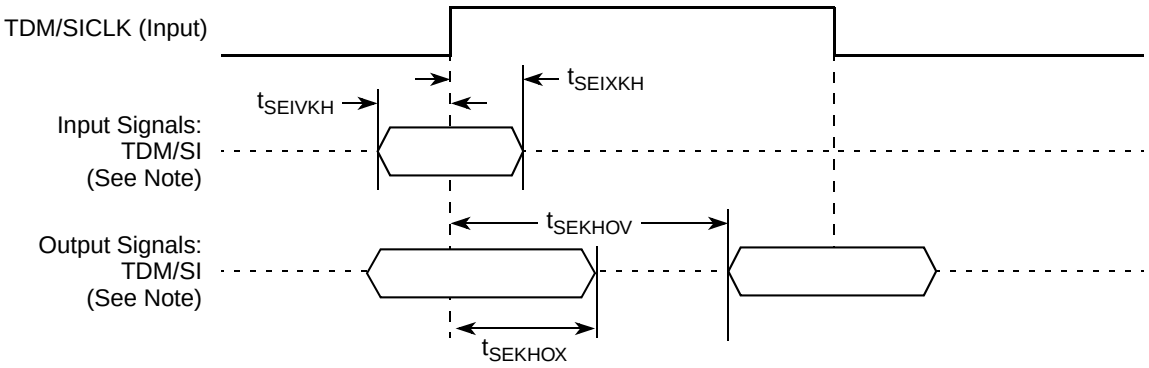
At recommended operating conditions (see Table 2).

Parameter	Symbol [2]	Min	Max	Unit	Notes
JTAG external clock frequency of operation	f_{JTG}	0	33.3	MHz	—
JTAG external clock cycle time	t_{JTG}	30	—	ns	—
JTAG external clock duty cycle	t_{JTKHKL}/t_{JTG}	45	55	%	—
JTAG external clock rise and fall times	t_{JTGR} & t_{JTGF}	0	2	ns	—
$\overline{\text{TRST}}$ assert time	t_{TRST}	25	—	ns	3
Input setup times: Boundary-scan data TMS, TDI	 t_{JTDVKH} t_{JTIVKH}	 4 4	 — —	ns	4
Input hold times: Boundary-scan data TMS, TDI	 t_{JTDXKH} t_{JTIXKH}	 10 10	 — —	ns	4
Valid times: Boundary-scan data TDO	 t_{JTKLDV} t_{JTKLOV}	 2 2	 11 11	ns	5
Output hold times: Boundary-scan data TDO	 t_{JTKLDX} t_{JTKLOX}	 2 2	 — —	ns	5
JTAG external clock to output high impedance: Boundary-scan data TDO	 t_{JTKLDZ} t_{JTKLOZ}	 2 2	 19 9	ns	5, 6

Notes:

1. All outputs are measured from the midpoint voltage of the falling/rising edge of t_{TCLK} to the midpoint of the signal in question. The output timings are measured at the pins. All output timings assume a purely resistive 50-Ω load (see Figure 22). Time-of-flight delays must be added for trace lengths, vias, and connectors in the system.
2. The symbols used for timing specifications herein follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{JTDVKH} symbolizes JTAG device timing (JT) with respect to the time data input signals (D) reaching the valid state (V) relative to the t_{JTG} clock reference (K) going to the high (H) state or setup time. Also, t_{JTDXKH} symbolizes JTAG timing (JT) with respect to the time data input signals (D) went invalid (X) relative to the t_{JTG} clock reference (K) going to the high (H) state. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
3. $\overline{\text{TRST}}$ is an asynchronous level sensitive signal. The setup time is for test purposes only.
4. Non-JTAG signal input timing with respect to t_{TCLK}.
5. Non-JTAG signal output timing with respect to t_{TCLK}.
6. Guaranteed by design and characterization.

This figure shows the TDM/SI timing with external clock.



Note: The clock edge is selectable on TDM/SI

Figure 45. TDM/SI AC Timing (External Clock) Diagram

17.3 UTOPIA/POS

This section describes the DC and AC electrical specifications for the UTOPIA/POS of the MPC8360E/58E.

17.4 UTOPIA/POS DC Electrical Characteristics

This table provides the DC electrical characteristics for the device UTOPIA.

Table 59. UTOPIA DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit
Output high voltage	V_{OH}	I_{OH} = –8.0 mA	2.4	—	V
Output low voltage	V_{OL}	I_{OL} = 8.0 mA	—	0.5	V
Input high voltage	V_{IH}	—	2.0	OV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	–0.3	0.8	V
Input current	I_{IN}	0 V ≤V_{IN} ≤OV_{DD}	—	±10	μA

17.5 UTOPIA/POS AC Timing Specifications

This table provides the UTOPIA input and output AC timing specifications.

Table 60. UTOPIA AC Timing Specifications[1]

Characteristic	Symbol[2]	Min	Max	Unit	Notes
UTOPIA outputs—Internal clock delay	t_{UIKHOV}	0	11.5	ns	—
UTOPIA outputs—External clock delay	t_{UEKHOV}	1	11.6	ns	—
UTOPIA outputs—Internal clock high impedance	t_{UIKHOX}	0	8.0	ns	—
UTOPIA outputs—External clock high impedance	t_{UEKHOX}	1	10.0	ns	—
UTOPIA inputs—Internal clock input setup time	t_{UIIVKH}	6	—	ns	—
UTOPIA inputs—External clock input setup time	t_{UEIVKH}	4	—	ns	3

Table 62. HDLC, BISYNC, and Transparent AC Timing Specifications[1] (continued)

Characteristic	Symbol[2]	Min	Max	Unit
Outputs—Internal clock high impedance	t_{HIKHOX}	-0.5	5.5	ns
Outputs—External clock high impedance	t_{HEKHOX}	1	8	ns
Inputs—Internal clock input setup time	t_{HIIVKH}	8.5	—	ns
Inputs—External clock input setup time	t_{HEIVKH}	4	—	ns
Inputs—Internal clock input hold time	t_{HIIXKH}	1.4	—	ns
Inputs—External clock input hold time	t_{HEIXKH}	1	—	ns

Notes:

1. Output specifications are measured from the 50% level of the rising edge of CLKIN to the 50% level of the signal. Timings are measured at the pin.
2. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{HIKHOX} symbolizes the outputs internal timing (HI) for the time t_{serial} memory clock reference (K) goes from the high state (H) until outputs (O) are invalid (X).

Table 63. Synchronous UART AC Timing Specifications[1]

Characteristic	Symbol[2]	Min	Max	Unit
Outputs—Internal clock delay	$t_{UAIKHOV}$	0	11.3	ns
Outputs—External clock delay	$t_{UAEKHOV}$	1	14	ns
Outputs—Internal clock high impedance	$t_{UAIKHOX}$	0	11	ns
Outputs—External clock high impedance	$t_{UAEKHOX}$	1	14	ns
Inputs—Internal clock input setup time	$t_{UAIIVKH}$	6	—	ns
Inputs—External clock input setup time	$t_{UAEIVKH}$	8	—	ns
Inputs—Internal clock input hold time	$t_{UAIIXKH}$	1	—	ns
Inputs—External clock input hold time	$t_{UAEIXKH}$	1	—	ns

Notes:

1. Output specifications are measured from the 50% level of the rising edge of CLKIN to the 50% level of the signal. Timings are measured at the pin.
2. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{HIKHOX} symbolizes the outputs internal timing (HI) for the time t_{serial} memory clock reference (K) goes from the high state (H) until outputs (O) are invalid (X).

This figure provides the AC test load.

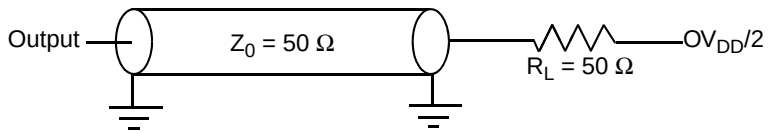


Figure 49. AC Test Load

Table 66. MPC8360E TBGA Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
PCI_DEVSEL/CE_PF[16]	E26	I/O	OV_{DD}	5
PCI_IDSEL/CE_PF[17]	F22	I/O	OV_{DD}	—
PCI_SERR/CE_PF[18]	B29	I/O	OV_{DD}	5
PCI_PERR/CE_PF[19]	A29	I/O	OV_{DD}	5
PCI_REQ[0]/CE_PF[20]	F19	I/O	$LV_{DD}2$	—
PCI_REQ[1]/CPCI_HS_ES/ CE_PF[21]	A21	I/O	$LV_{DD}2$	—
PCI_REQ[2]/CE_PF[22]	C21	I/O	$LV_{DD}2$	—
PCI_GNT[0]/CE_PF[23]	E20	I/O	$LV_{DD}2$	—
PCI_GNT[1]/CPCI1_HS_LED/ CE_PF[24]	B20	I/O	$LV_{DD}2$	—
PCI_GNT[2]/CPCI1_HS_ENUM/ CE_PF[25]	C20	I/O	$LV_{DD}2$	—
PCI_MODE	D36	I	OV_{DD}	—
M66EN/CE_PF[4]	B37	I/O	OV_{DD}	—
Local Bus Controller Interface				
LAD[0:31]	N32, N33, N35, N36, P37, P32, P34, R36, R35, R34, R33, T37, T35, T34, T33, U37, T32, U36, U34, V36, V35, W37, W35, V33, V32, W34, Y36, W32, AA37, Y33, AA35, AA34	I/O	OV_{DD}	—
LDP[0]/CKSTOP_OUT	AB37	I/O	OV_{DD}	—
LDP[1]/CKSTOP_IN	AB36	I/O	OV_{DD}	—
LDP[2]/LCS[6]	AB35	I/O	OV_{DD}	—
LDP[3]/LCS[7]	AA33	I/O	OV_{DD}	—
LA[27:31]	AC37, AA32, AC36, AC34, AD36	O	OV_{DD}	—
LCS[0:5]	AD33, AG37, AF34, AE33, AD32, AH37	O	OV_{DD}	—
LWE[0:3]/LSDDQM[0:3]/LBS[0:3]	AG35, AG34, AH36, AE32	O	OV_{DD}	—
LBCTL	AD35	O	OV_{DD}	—
LALE	M37	O	OV_{DD}	—
LGPL0/LSDA10/cfg_reset_source0	AB32	I/O	OV_{DD}	—
LGPL1/LSDWE/cfg_reset_source1	AE37	I/O	OV_{DD}	—
LGPL2/LSDRAS/LOE	AC33	O	OV_{DD}	—
LGPL3/LSDCAS/cfg_reset_source2	AD34	I/O	OV_{DD}	—
LGPL4/LGTA/LUPWAIT/LPBSE	AE35	I/O	OV_{DD}	—
LGPL5/cfg_clkin_div	AF36	I/O	OV_{DD}	—
LCKE	G36	O	OV_{DD}	—
LCLK[0]	J33	O	OV_{DD}	—
LCLK[1]/LCS[6]	J34	O	OV_{DD}	—

Table 67. MPC8358E TBGA Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
$\overline{\text{PORESET}}$	L37	I	OV_{DD}	—
$\overline{\text{HRESET}}$	L36	I/O	OV_{DD}	1
$\overline{\text{SRESET}}$	M33	I/O	OV_{DD}	2
Thermal Management				
THERM0	AP19	I	GV_{DD}	—
THERM1	AT31	I	GV_{DD}	—
Power and Ground Signals				
$AV_{DD}1$	K35	Power for LBIU DLL (1.2 V)	$AV_{DD}1$	—
$AV_{DD}2$	K36	Power for CE PLL (1.2 V)	$AV_{DD}2$	—
$AV_{DD}5$	AM29	Power for e300 PLL (1.2 V)	$AV_{DD}5$	—
$AV_{DD}6$	K37	Power for system PLL (1.2 V)	$AV_{DD}6$	—
GND	A2, A8, A13, A19, A22, A25, A31, A33, A36, B7, B12, B24, B27, B30, C4, C6, C9, C15, C26, C32, D3, D8, D11, D14, D17, D19, D23, D27, E7, E13, E25, E30, E36, F4, F37, G34, H1, H5, H32, H33, J4, J32, J37, K1, L3, L5, L33, L34, M1, M34, M35, N37, P2, P5, P35, P36, R4, T3, U1, U5, U35, V37, W1, W4, W33, W36, Y34, AA3, AA5, AC3, AC32, AC35, AD1, AD37, AE4, AE34, AE36, AF33, AG4, AG6, AG32, AH35, AJ1, AJ4, AJ32, AJ35, AJ37, AK36, AL3, AL34, AM4, AN6, AN23, AN30, AP8, AP12, AP14, AP16, AP17, AP20, AP25, AR6, AR8, AR9, AR19, AR24, AR31, AR35, AR37, AT4, AT10, AT19, AT20, AT25, AU14, AU22, AU28, AU35	—	—	—
GV_{DD}	AD4, AE3, AF1, AF5, AF35, AF37, AG2, AG36, AH33, AH34, AK5, AM1, AM35, AM37, AN2, AN10, AN11, AN12, AN14, AN32, AN36, AP5, AP23, AP28, AR1, AR7, AR10, AR12, AR21, AR25, AR27, AR33, AT15, AT22, AT28, AT33, AU2, AU5, AU16, AU31, AU36	Power for DDR DRAM I/O voltage (2.5 or 1.8 V)	GV_{DD}	—
$LV_{DD}0$	D5, D6	Power for UCC1 Ethernet interface (2.5 V, 3.3 V)	$LV_{DD}0$	—

Table 74. QUICC Engine Block PLL Multiplication Factors (continued)

RCWL[CEPMF]	RCWL[CEPDF]	QUICC Engine PLL Multiplication Factor = RCWL[CEPMF]/ (1 + RCWL[CEPDF])
11101	0	× 29
11110	0	× 30
11111	0	× 31
00011	1	× 1.5
00101	1	× 2.5
00111	1	× 3.5
01001	1	× 4.5
01011	1	× 5.5
01101	1	× 6.5
01111	1	× 7.5
10001	1	× 8.5
10011	1	× 9.5
10101	1	× 10.5
10111	1	× 11.5
11001	1	× 12.5
11011	1	× 13.5
11101	1	× 14.5

Note:
1. Reserved modes are not listed.

The RCWL[CEVCOD] denotes the QUICC Engine Block PLL VCO internal frequency as shown in this table.

Table 75. QUICC Engine Block PLL VCO Divider

RCWL[CEVCOD]	VCO Divider
00	4
01	8
10	2
11	Reserved

NOTE

The VCO divider (RCWL[CEVCOD]) must be set properly so that the QUICC Engine block VCO frequency is in the range of 600–1400 MHz. The QUICC Engine block frequency is not restricted by the CSB and core frequencies. The CSB, core, and QUICC Engine block frequencies should be selected according to the performance requirements.

Table 77. Package Thermal Characteristics for the TBGA Package (continued)

Characteristic	Symbol	Value	Unit	Notes
Junction-to-package natural convection on top	Ψ_{JT}	1	°C/W	6

Notes

1. Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, airflow, power dissipation of other components on the board, and board thermal resistance.
2. Per JEDEC JESD51-2 and SEMI G38-87 with the single layer board horizontal.
3. Per JEDEC JESD51-6 with the board horizontal. 1 m/sec is approximately equal to 200 linear feet per minute (LFM).
4. Thermal resistance between the die and the printed-circuit board per JEDEC JESD51-8. Board temperature is measured on the top surface of the board near the package.
5. Thermal resistance between the die and the case top surface as measured by the cold plate method (MIL SPEC-883 Method 1012.1).
6. Thermal characterization parameter indicating the temperature difference between package top and the junction temperature per JEDEC JESD51-2. When Greek letters are not available, the thermal characterization parameter is written as Psi-JT.

22.2 Thermal Management Information

For the following sections, $P_D = (V_{DD} \times I_{DD}) + P_{I/O}$ where $P_{I/O}$ is the power dissipation of the I/O drivers. See Table 6 for typical power dissipations values.

22.2.1 Estimation of Junction Temperature with Junction-to-Ambient Thermal Resistance

An estimation of the chip junction temperature, T_J, can be obtained from the equation:

$$T_J = T_A + (R_{\theta JA} \times P_D)$$

where:

T_J = junction temperature (°C)
T_A = ambient temperature for the package (°C)
$R_{\theta JA}$ = junction-to-ambient thermal resistance (°C/W)
P_D = power dissipation in the package (W)

The junction-to-ambient thermal resistance is an industry standard value that provides a quick and easy estimation of thermal performance. As a general statement, the value obtained on a single-layer board is appropriate for a tightly packed printed-circuit board. The value obtained on the board with the internal planes is usually appropriate if the board has low power dissipation and the components are well separated. Test cases have demonstrated that errors of a factor of two (in the quantity $T_J - T_A$) are possible.

22.2.2 Estimation of Junction Temperature with Junction-to-Board Thermal Resistance

The thermal performance of a device cannot be adequately predicted from the junction-to-ambient thermal resistance. The thermal performance of any component is strongly dependent on the power dissipation of surrounding components. Additionally, the ambient temperature varies widely within the application. For many natural convection and especially closed box applications, the board temperature at the perimeter (edge) of the package is approximately the same as the local air temperature near the device. Specifying the local ambient conditions explicitly as the board temperature provides a more precise description of the local ambient conditions that determine the temperature of the device. At a known board temperature, the junction temperature is estimated using the following equation:

$$T_J = T_B + (R_{\theta JB} \times P_D)$$

where:

T_J = junction temperature (° C)
T_B = board temperature at the package perimeter (° C)
$R_{\theta JA}$ = junction to board thermal resistance (° C/W) per JESD51-8
P_D = power dissipation in the package (W)

When the heat loss from the package case to the air can be ignored, acceptable predictions of junction temperature can be made. The application board should be similar to the thermal test condition: the component is soldered to a board with internal planes.

22.2.3 Experimental Determination of Junction Temperature

To determine the junction temperature of the device in the application after prototypes are available, the Thermal Characterization Parameter (Ψ_{JT}) can be used to determine the junction temperature with a measurement of the temperature at the top center of the package case using the following equation:

$$T_J = T_T + (\Psi_{JT} \times P_D)$$

where:

T_J = junction temperature (° C)
T_T = thermocouple temperature on top of package (° C)
Ψ_{JT} = junction-to-ambient thermal resistance (° C/W)
P_D = power dissipation in the package (W)

The thermal characterization parameter is measured per JESD51-2 specification using a 40 gauge type T thermocouple epoxied to the top center of the package case. The thermocouple should be positioned so that the thermocouple junction rests on the package. A small amount of epoxy is placed over the thermocouple junction and over about 1 mm of wire extending from the junction. The thermocouple wire is placed flat against the package case to avoid measurement errors caused by cooling effects of the thermocouple wire.

22.2.4 Heat Sinks and Junction-to-Ambient Thermal Resistance

In some application environments, a heat sink is required to provide the necessary thermal management of the device. When a heat sink is used, the thermal resistance is expressed as the sum of a junction to case thermal resistance and a case to ambient thermal resistance:

$$R_{\theta JA} = R_{\theta JC} + R_{\theta CA}$$

where:

$R_{\theta JA}$ = junction-to-ambient thermal resistance (° C/W)
$R_{\theta JC}$ = junction-to-case thermal resistance (° C/W)
$R_{\theta CA}$ = case-to-ambient thermal resistance (° C/W)

$R_{\theta JC}$ is device related and cannot be influenced by the user. The user controls the thermal environment to change the case-to-ambient thermal resistance, $R_{\theta CA}$. For instance, the user can change the size of the heat sink, the airflow around the device, the interface material, the mounting arrangement on printed-circuit board, or change the thermal dissipation on the printed-circuit board surrounding the device.

To illustrate the thermal performance of the devices with heat sinks, the thermal performance has been simulated with a few commercially available heat sinks. The heat sink choice is determined by the application environment (temperature, airflow, adjacent component power dissipation) and the physical space available. Because there is not a standard application environment, a standard heat sink is not required.

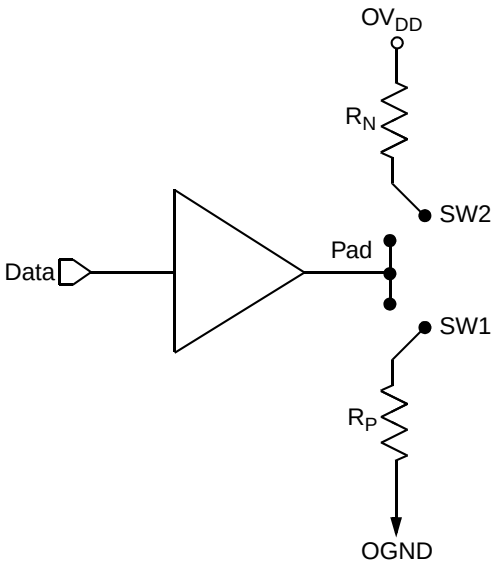


Figure 57. Driver Impedance Measurement

The value of this resistance and the strength of the driver's current source can be found by making two measurements. First, the output voltage is measured while driving logic 1 without an external differential termination resistor. The measured voltage is $V_1 = R_{source} \times I_{source}$. Second, the output voltage is measured while driving logic 1 with an external precision differential termination resistor of value R_{term}. The measured voltage is $V_2 = 1/(1/R_1 + 1/R_2)) \times I_{source}$. Solving for the output impedance gives $R_{source} = R_{term} \times (V_1/V_2 - 1)$. The drive current is then $I_{source} = V_1/R_{source}$.

This table summarizes the signal impedance targets. The driver impedance are targeted at minimum V_{DD}, nominal OV_{DD}, 105° C.

Table 79. Impedance Characteristics

Impedance	Local Bus, Ethernet, DUART, Control, Configuration, Power Management	PCI	DDR DRAM	Symbol	Unit
R_N	42 Target	25 Target	20 Target	Z_0	W
R_P	42 Target	25 Target	20 Target	Z_0	W
Differential	NA	NA	NA	Z_{DIFF}	W

Note: Nominal supply voltages. See Table 1, T_J = 105° C.

23.6 Configuration Pin Muxing

The device provides the user with power-on configuration options that can be set through the use of external pull-up or pull-down resistors of 4.7 kΩ on certain output pins (see customer visible configuration pins). These pins are generally used as output only pins in normal operation.

While $\overline{\text{HRESET}}$ is asserted however, these pins are treated as inputs. The value presented on these pins while $\overline{\text{HRESET}}$ is asserted, is latched when $\overline{\text{HRESET}}$ deasserts, at which time the input receiver is disabled and the I/O circuit takes on its normal function. Careful board layout with stubless connections to these pull-up/pull-down resistors coupled with the large value of the pull-up/pull-down resistor should minimize the disruption of signal quality or speed for output pins thus configured.

23.7 Pull-Up Resistor Requirements

The device requires high resistance pull-up resistors (10 kΩ is recommended) on open drain type pins including I^2C pins, Ethernet Management MDIO pin, and EPIC interrupt pins.

For more information on required pull-up resistors and the connections required for the JTAG interface, see *MPC8360E/MPC8358E PowerQUICC Design Checklist* (AN3097).

24 Ordering Information

24.1 Part Numbers Fully Addressed by this Document

This table provides the Freescale part numbering nomenclature for the MPC8360E/58E. Note that the individual part numbers correspond to a maximum processor core frequency. For available frequencies, contact your local Freescale sales office. Additionally to the processor frequency, the part numbering scheme also includes an application modifier, which may specify special application conditions. Each part number also contains a revision code that refers to the die mask revision number.

Table 80. Part Numbering Nomenclature[1]

MPC	***nnnn***	***e***	***t***	***pp***	***aa***	***a***	***a***	***A***
Product Code	**Part Identifier**	**Encryption Acceleration**	**Temperature Range**	**Package[2]**	**Processor Frequency[3]**	**Platform Frequency**	**QUICC Engine Frequency**	**Die Revision**
MPC	8358	Blank = not included E = included	Blank = 0° C T_A to 105° C T_J C= –40° C T_A to 105° C T_J	ZU = TBGA VV = TBGA (no lead)	e300 core speed AD = 266 MHz AG = 400 MHz	D = 266 MHz	E = 300 MHz G = 400 MHz	A = rev. 2.1 silicon
	8360				e300 core speed AG = 400 MHz AJ = 533 MHz AL = 667 MHz	D = 266 MHz F = 333 MHz	G = 400 MHz H = 500 MHz	A = rev. 2.1 silicon
MPC (rev. 2.0 silicon only)	8360	Blank = not included E = included	0° C T_A to 70° C T_J	ZU = TBGA VV = TBGA (no lead)	e300 core speed AH = 500 MHz AL = 667 MHz	F = 333 MHz	G = 400 MHz H = 500 MHz	—

Notes:

1. Not all processor, platform, and QUICC Engine block frequency combinations are supported. For available frequency combinations, contact your local Freescale sales office or authorized distributor.
2. See Section 20, "Package and Pin Listings," for more information on available package types.
3. Processor core frequencies supported by parts addressed by this specification only. Not all parts described in this specification support all core frequencies. Additionally, parts addressed by part number specifications may support other maximum core frequencies.

This table shows the SVR settings by device and package type.

Table 81. SVR Settings

Device	Package	SVR (Rev. 2.0)	SVR (Rev. 2.1)
MPC8360E	TBGA	0x8048_0020	0x8048_0021
MPC8360	TBGA	0x8049_0020	0x8049_0021

Table 81. SVR Settings (continued)

Device	Package	SVR (Rev. 2.0)	SVR (Rev. 2.1)
MPC8358E	TBGA	0x804A_0020	0x804A_0021
MPC8358	TBGA	0x804B_0020	0x804B_0021

25 Document Revision History

This table provides a revision history for this document.

Table 82. Revision History

Rev. Number	Date	Substantive Change(s)
5	09/2011	• Section 2.2.1, “Power-Up Sequencing”, added the current limitation “3A to 5A” for the excessive current. • Section 2.1.2, “Power Supply Voltage Specification, Updated the Characteristic for TBGA (MPC8358 & MPC8360 Device) with specific frequency for Core and PLL voltages. • Added table footnote 3 to Table 2. • Applied table footnotes 1 and 2 to Table 10. • Removed table footnotes from Table 19. • Applied table footnote 8 to the last row of Table 40. • Applied table footnotes 8 and 9 to Table 41. • Applied table footnotes 2and 3 to Table 45. • Removed table footnotes from Table 46. • Applied table footnote to last three rows of Table 65.
4	01/2011	• Updated references to the LCRR register throughout • Removed references to DDR DLL mode in Section 6.2.2, “DDR and DDR2 SDRAM Output AC Timing Specifications.” • Changed “Junction-to-Case” to “Junction-to-Ambient” in Section 22.2.4, “Heat Sinks and Junction-to-Ambient Thermal Resistance,” and Table 78, “Heat Sinks and Junction-to-Ambient Thermal Resistance of TBGA Package,” titles.